

Features

- 650 Volt Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters

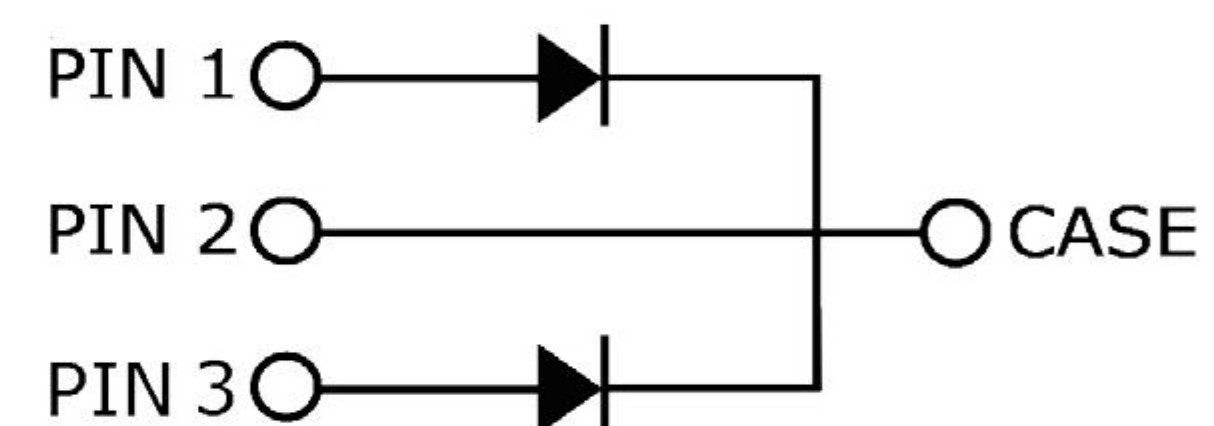
| Part Number | Package | Marking |
|-------------|----------|----------|
| C3D30065D | TO-247-3 | C3D30065 |



TO-247-3

| | | |
|-------------------------------|---|---------|
| V_{RRM} | = | 650 V |
| $I_F (T_C=135^\circ\text{C})$ | = | 36 A** |
| Q_c | = | 89 nC** |

Package



Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Value | | Test Conditions | Note |
|----------------|---|-------------------------|------------------|---|--------|
| V_{RRM} | Repetitive Peak Reverse Voltage | 650 | V | | |
| V_{RSM} | Surge Peak Reverse Voltage | 650 | V | | |
| V_{DC} | DC Blocking Voltage | 650 | V | | |
| I_F | Continuous Forward Current (Per Leg/Device) | 39/78 18/36 15/30 | A | $T_C=25^\circ\text{C}$ $T_C=135^\circ\text{C}$ $T_C=145^\circ\text{C}$ | Fig. 3 |
| I_{FRM} | Repetitive Peak Forward Surge Current | 66* 46* | A | $T_C=25^\circ\text{C}, t_p=10\text{ ms}$, Half Sine Pulse $T_C=110^\circ\text{C}, t_p=10\text{ ms}$, Half Sine Pulse | |
| I_{FSM} | Non-Repetitive Peak Forward Surge Current | 162 150 | A | $T_C=25^\circ\text{C}, t_p=10\text{ ms}$, Half Sine Pulse $T_C=110^\circ\text{C}, t_p=10\text{ ms}$, Half Sine Pulse | Fig. 8 |
| $I_{F,Max}$ | Non-Repetitive Peak Forward Current | 1400 1200 | A | $T_C=25^\circ\text{C}, t_p=10\text{ }\mu\text{s}$, Pulse $T_C=110^\circ\text{C}, t_p=10\text{ }\mu\text{s}$, Pulse | Fig. 8 |
| P_{tot} | Power Dissipation(Per Leg/Device) | 150 65 | W | $T_C=25^\circ\text{C}$ $T_C=110^\circ\text{C}$ | Fig. 4 |
| dV/dt | Diode dV/dt ruggedness | 200 | V/ns | $V_R=0-600\text{V}$ | |
| $\int i^2 dt$ | i^2t value | 131* 112.5* | A ² s | $T_C=25^\circ\text{C}, t_p=10\text{ ms}$ $T_C=110^\circ\text{C}, t_p=10\text{ ms}$ | |
| T_J, T_{stg} | Operating Junction and Storage Temperature | -55 to +175 | $^\circ\text{C}$ | | |
| | TO-247 Mounting Torque | 1 8.8 | Nm lbf-in | M3 Screw 6-32 Screw | |

* Per Leg, ** Per Device

Electrical Characteristics (Per Leg)

| Symbol | Parameter | Typ. | Max. | Unit | Test Conditions | Note |
|--------|---------------------------|-------------------|------------|---------------|--|--------|
| V_F | Forward Voltage | 1.45 2.0 | 1.8 2.4 | V | $I_F = 16\text{ A } T_J = 25^\circ\text{C}$ $I_F = 16\text{ A } T_J = 175^\circ\text{C}$ | Fig. 1 |
| I_R | Reverse Current | 18.5 38.5 | 95 378 | μA | $V_R = 650\text{ V } T_J = 25^\circ\text{C}$ $V_R = 650\text{ V } T_J = 175^\circ\text{C}$ | Fig. 2 |
| Q_C | Total Capacitive Charge | 44.5 | | nC | $V_R = 400\text{ V}, I_F = 16\text{ A}$ $di/dt = 500\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$ | Fig. 5 |
| C | Total Capacitance | 877.5 80 64 | | pF | $V_R = 0\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$ $V_R = 200\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$ $V_R = 400\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$ | Fig. 6 |
| E_C | Capacitance Stored Energy | 6.2 | | μJ | $V_R = 400\text{ V}$ | Fig. 7 |

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

| Symbol | Parameter | Typ. | Unit | Note |
|-----------------|--|-------------|---------------------------|--------|
| $R_{\theta JC}$ | Thermal Resistance from Junction to Case | 1* 0.5** | $^\circ\text{C}/\text{W}$ | Fig. 9 |

* Per Leg, ** Per Device

Typical Performance (Per Leg)

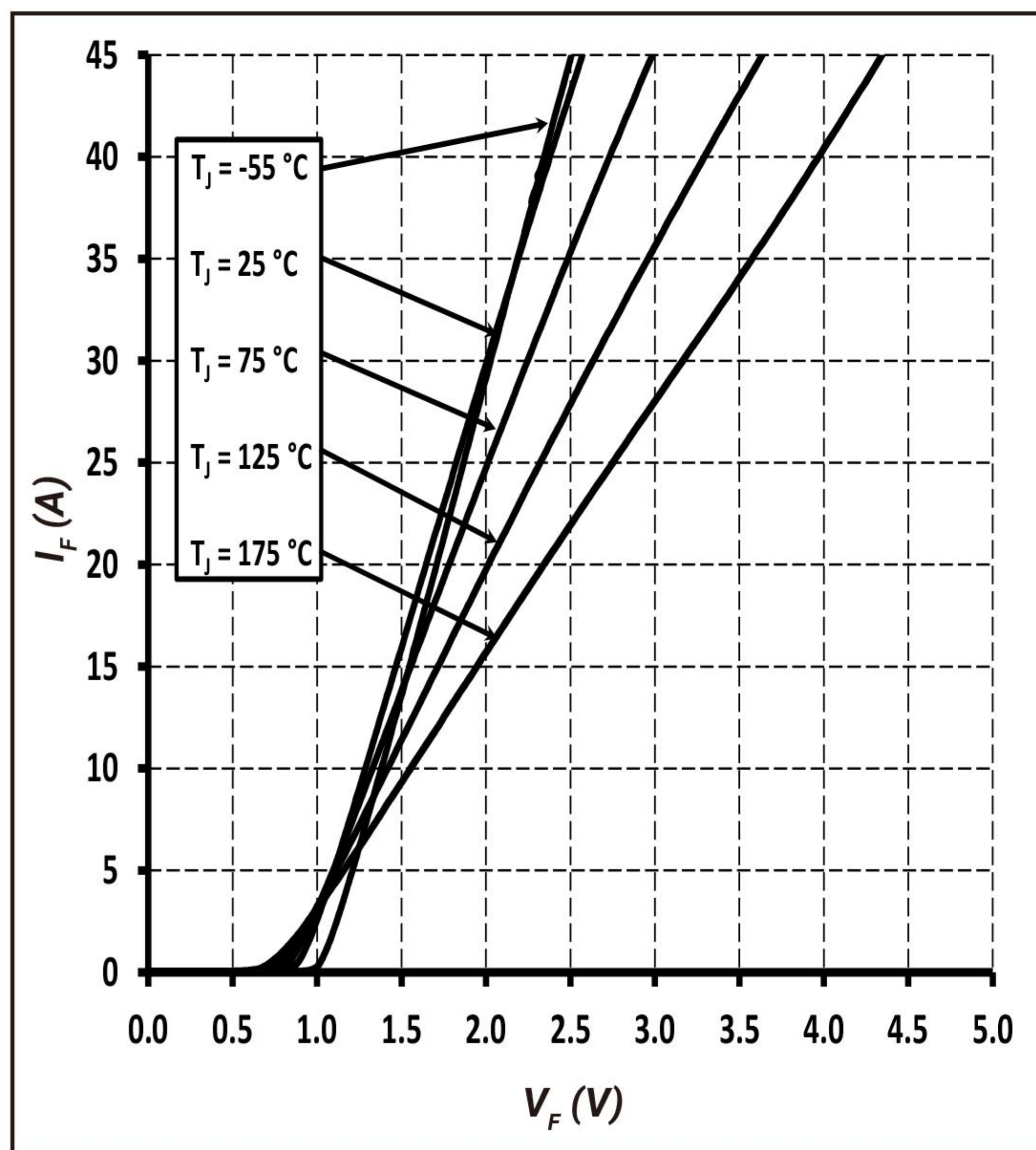


Figure 1. Forward Characteristics

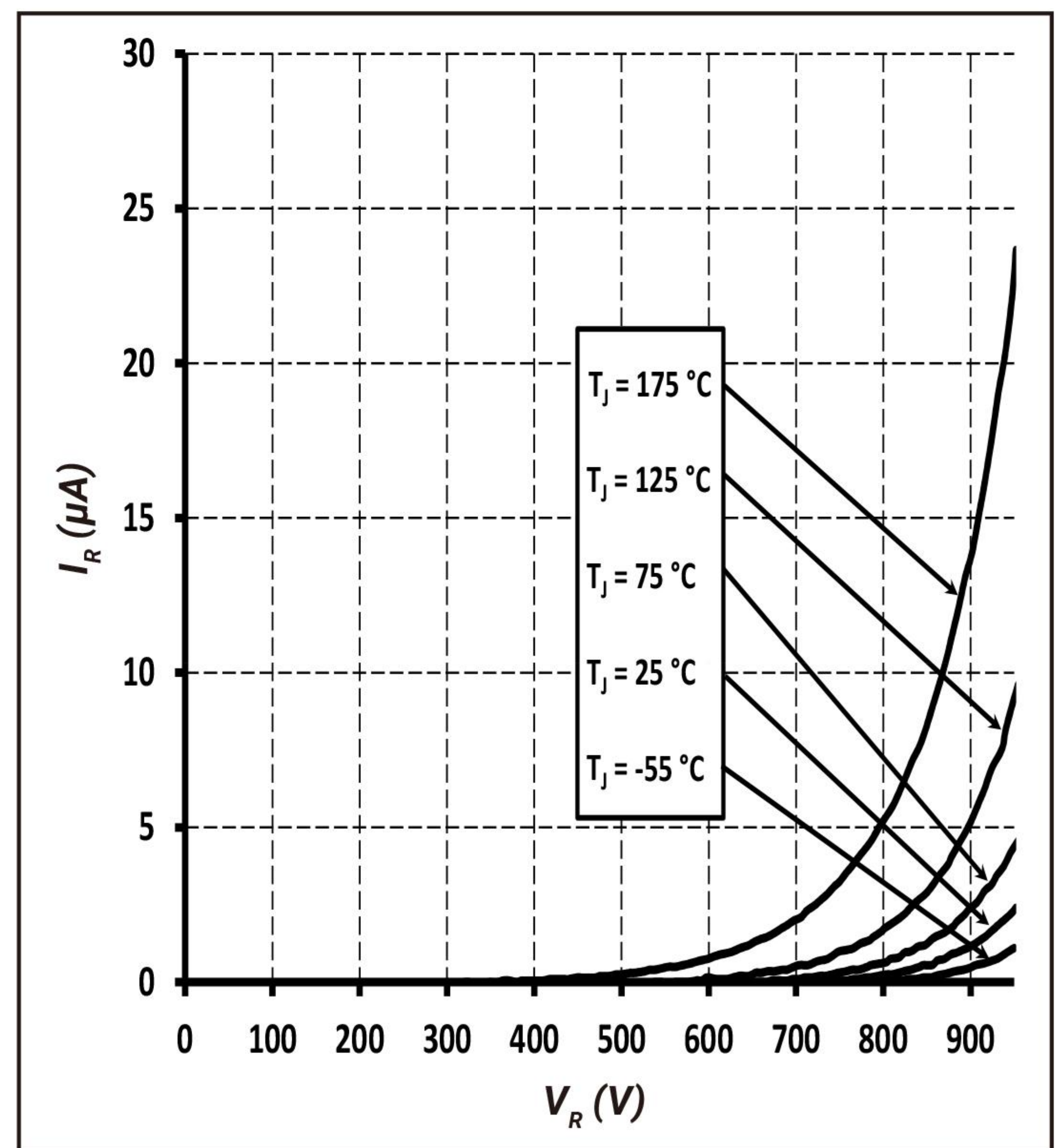


Figure 2. Reverse Characteristics

Typical Performance (Per Leg)

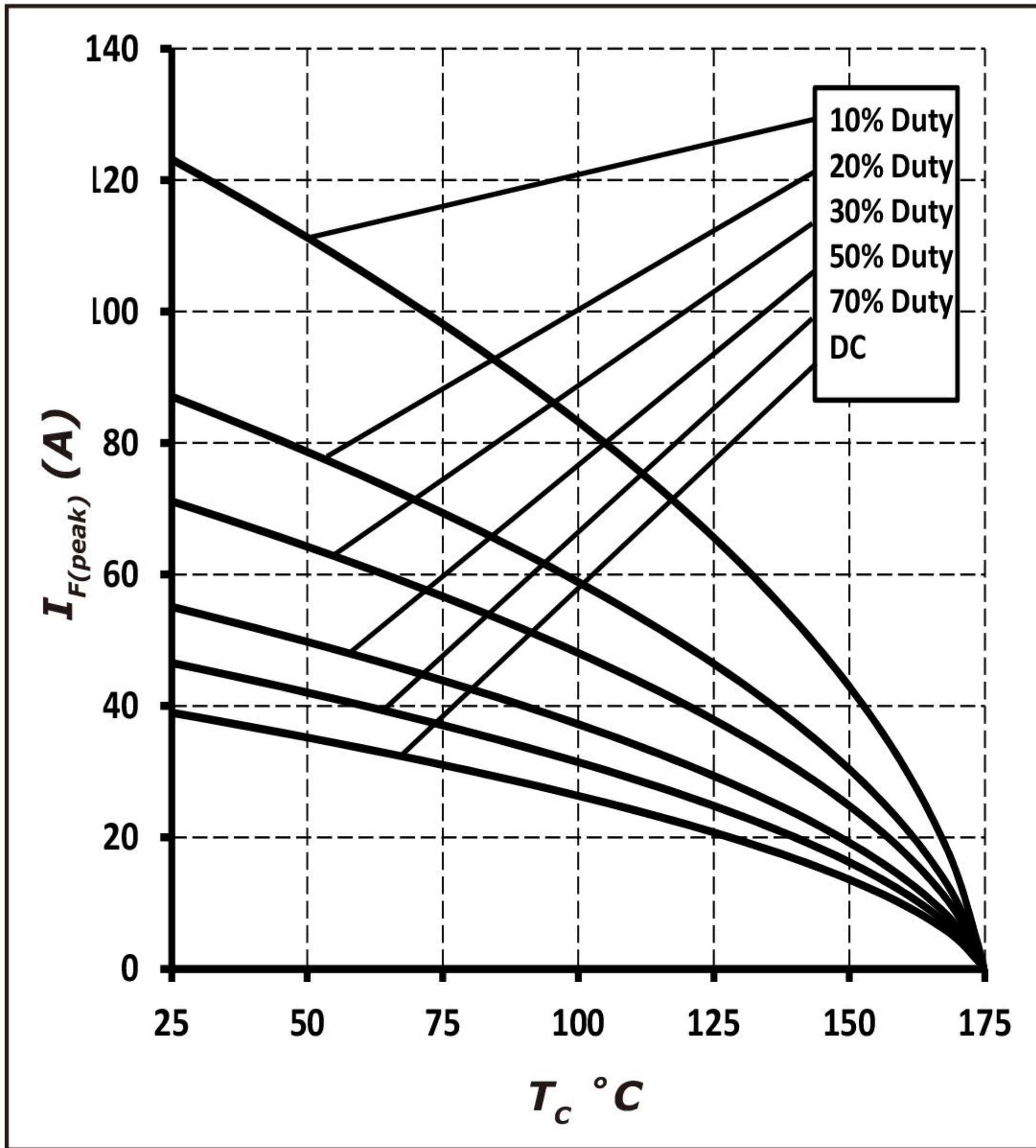


Figure 3. Current Derating

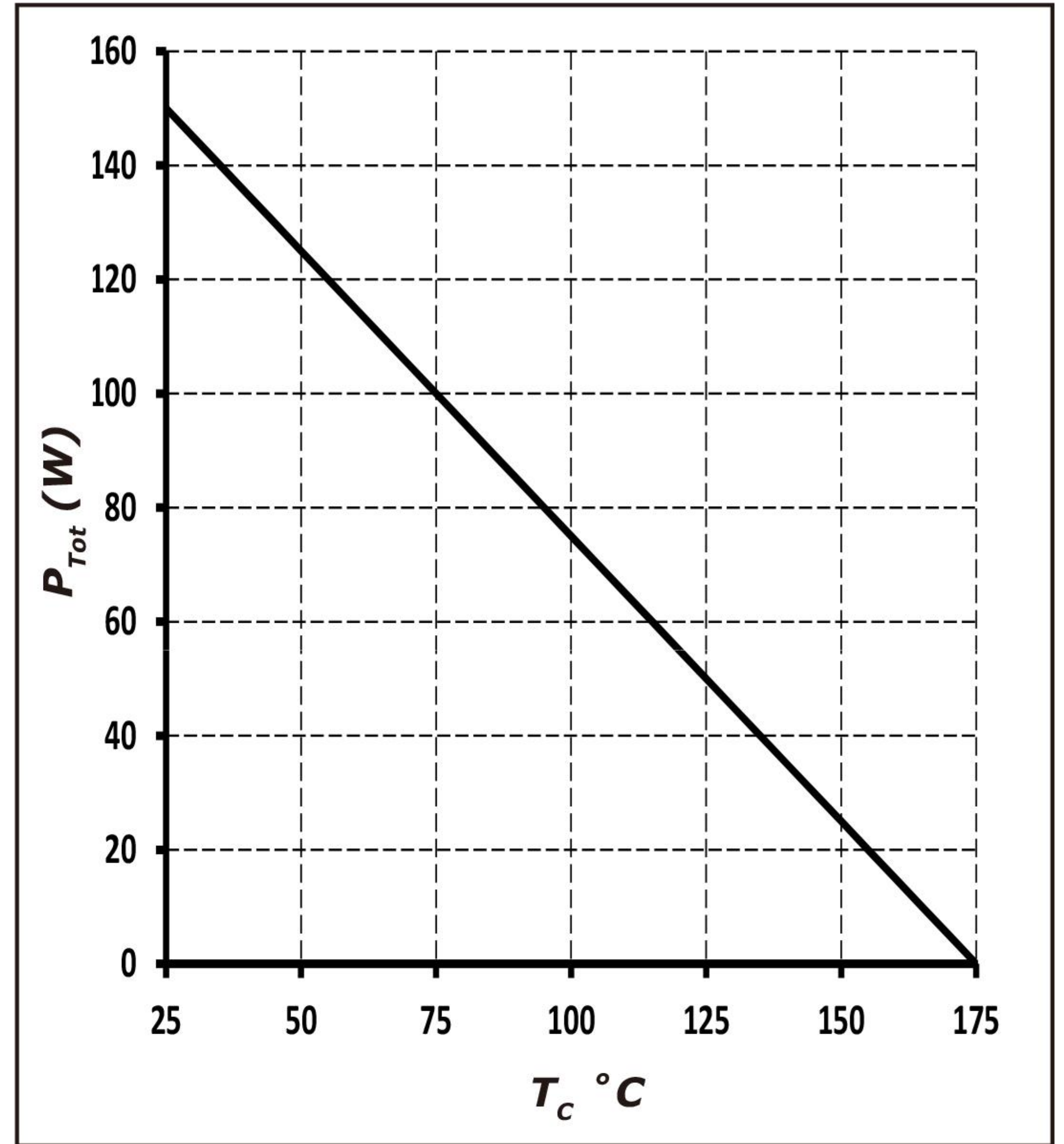


Figure 4. Power Derating

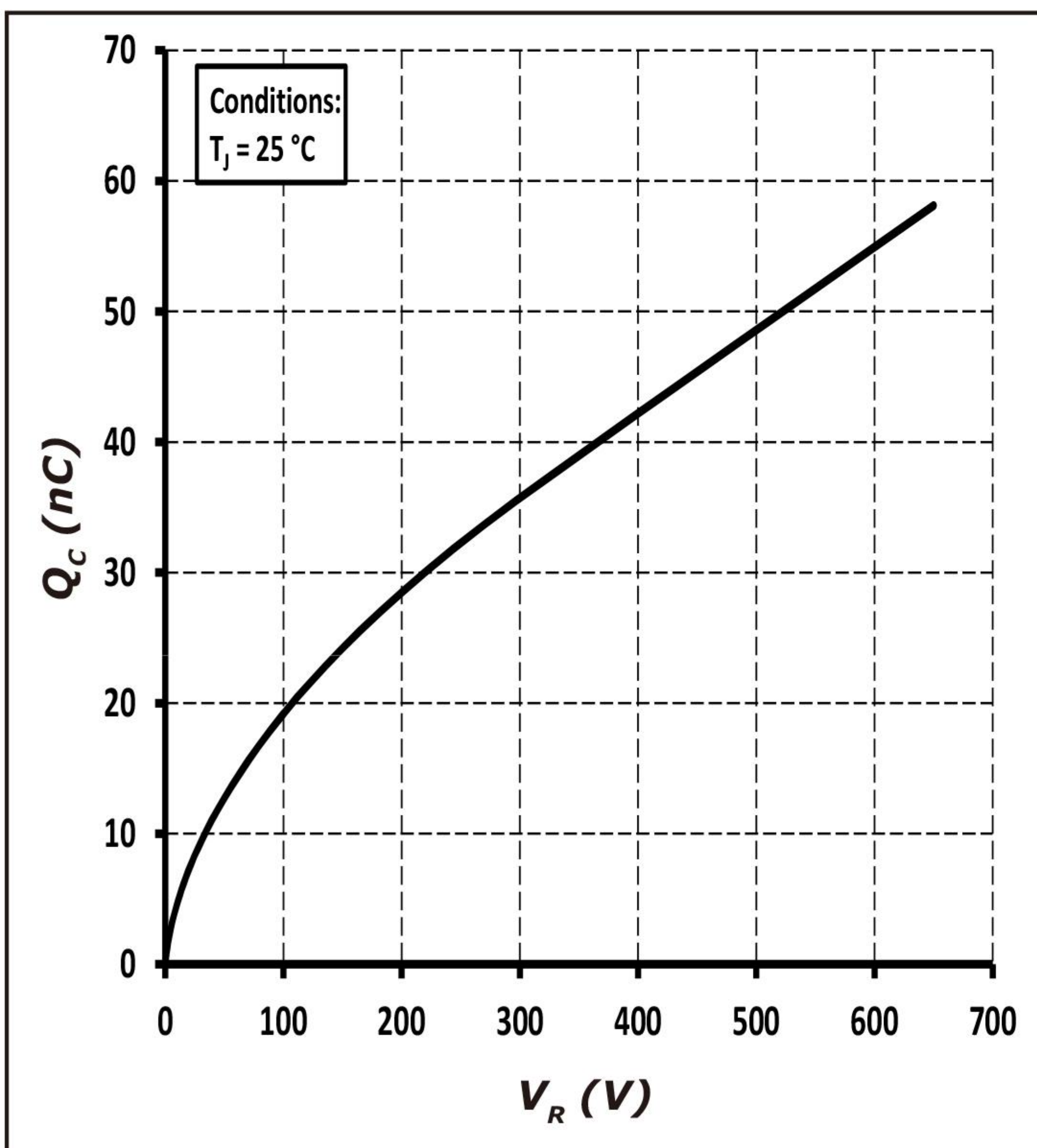


Figure 5. Total Capacitance Charge vs. Reverse Voltage

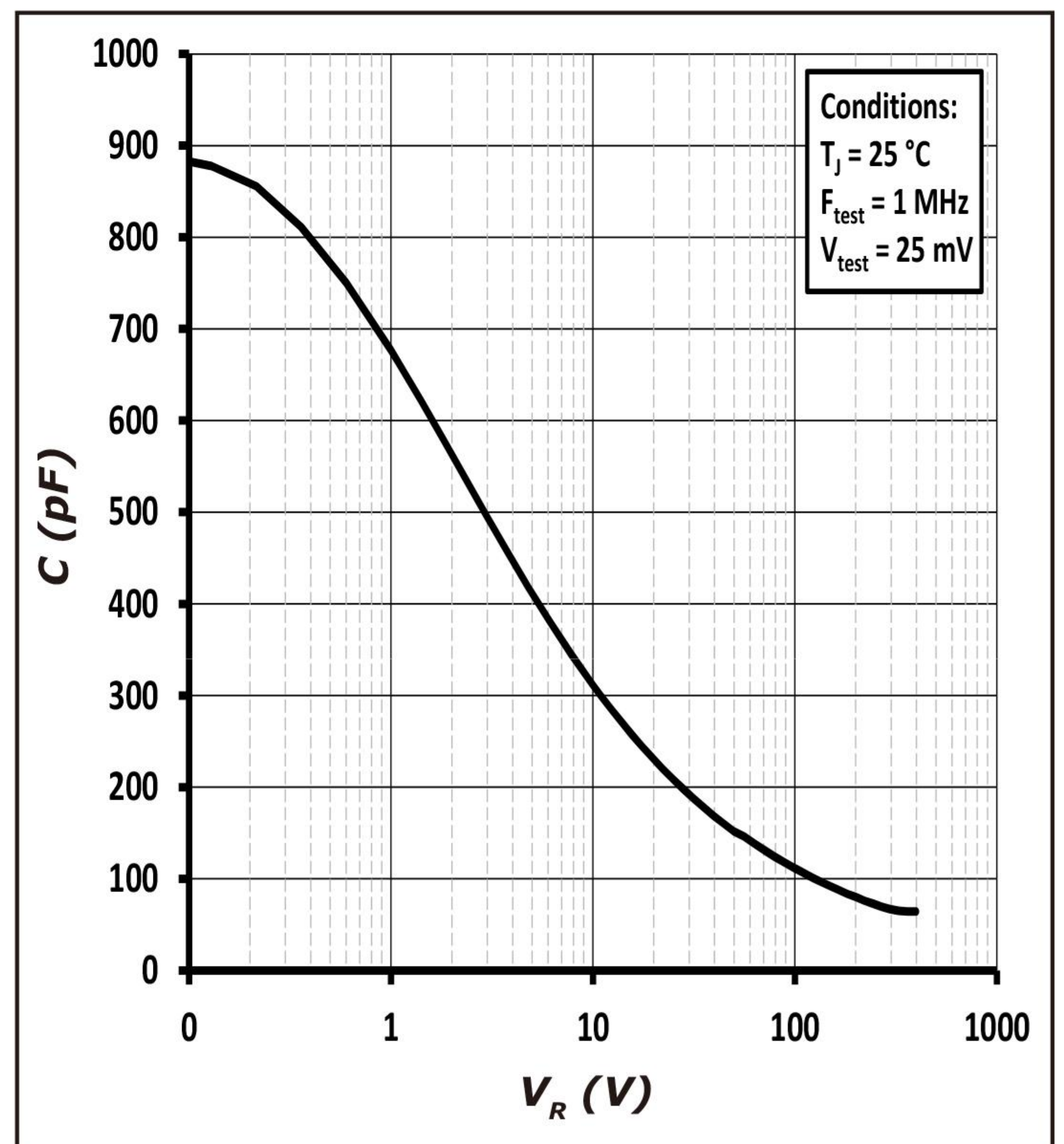


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance (Per Leg)

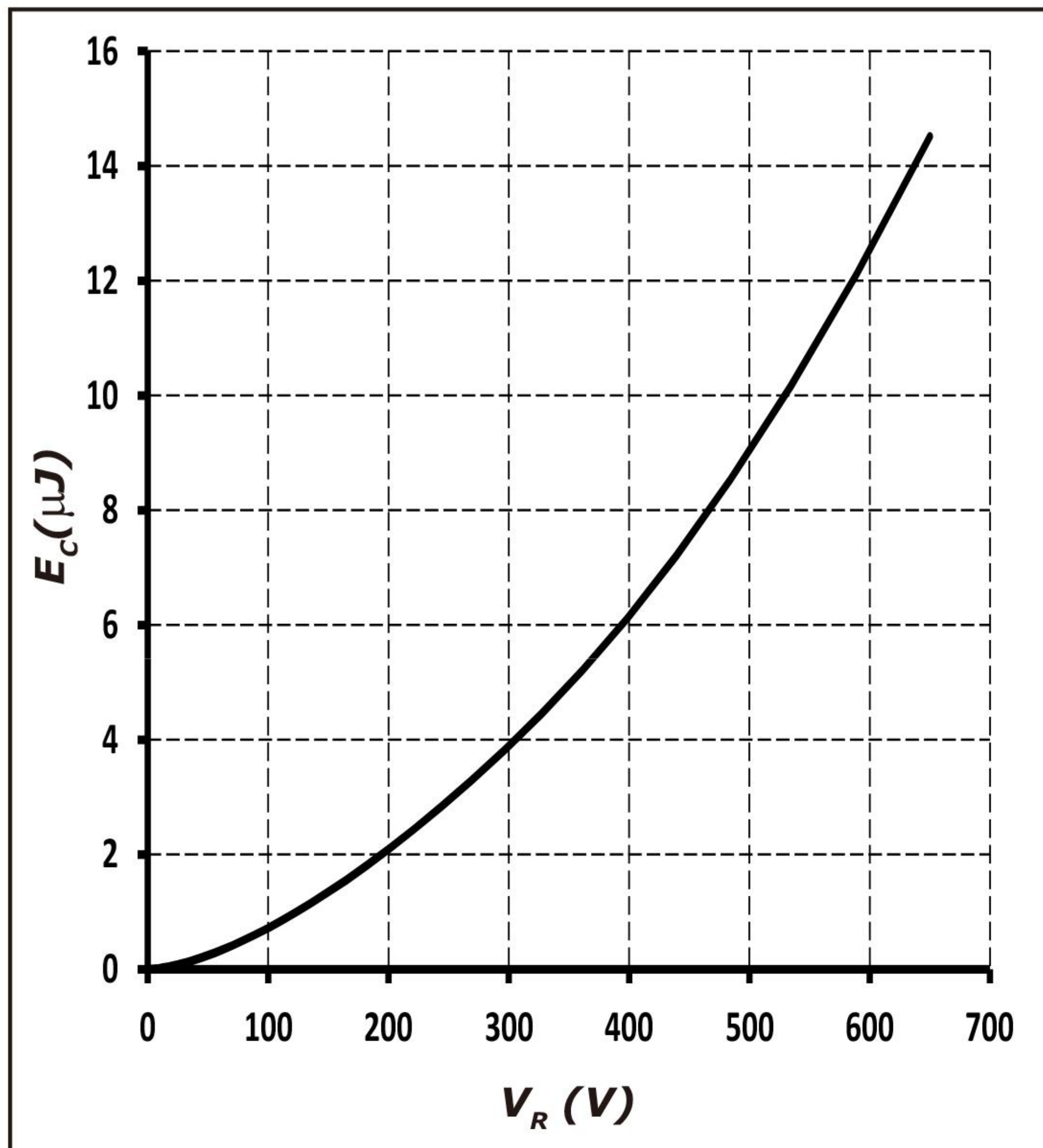


Figure 7. Capacitance Stored Energy

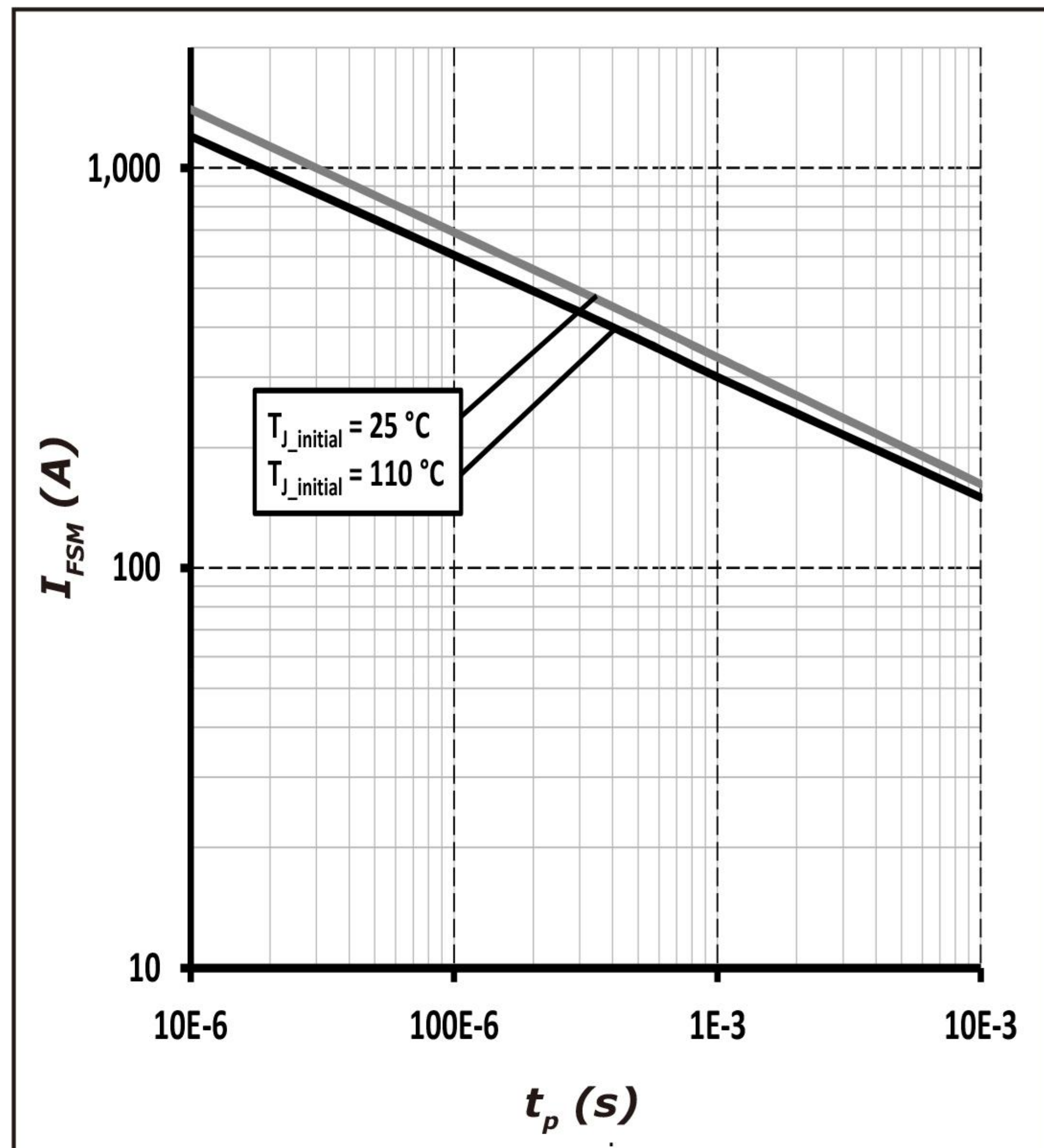


Figure 8. Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

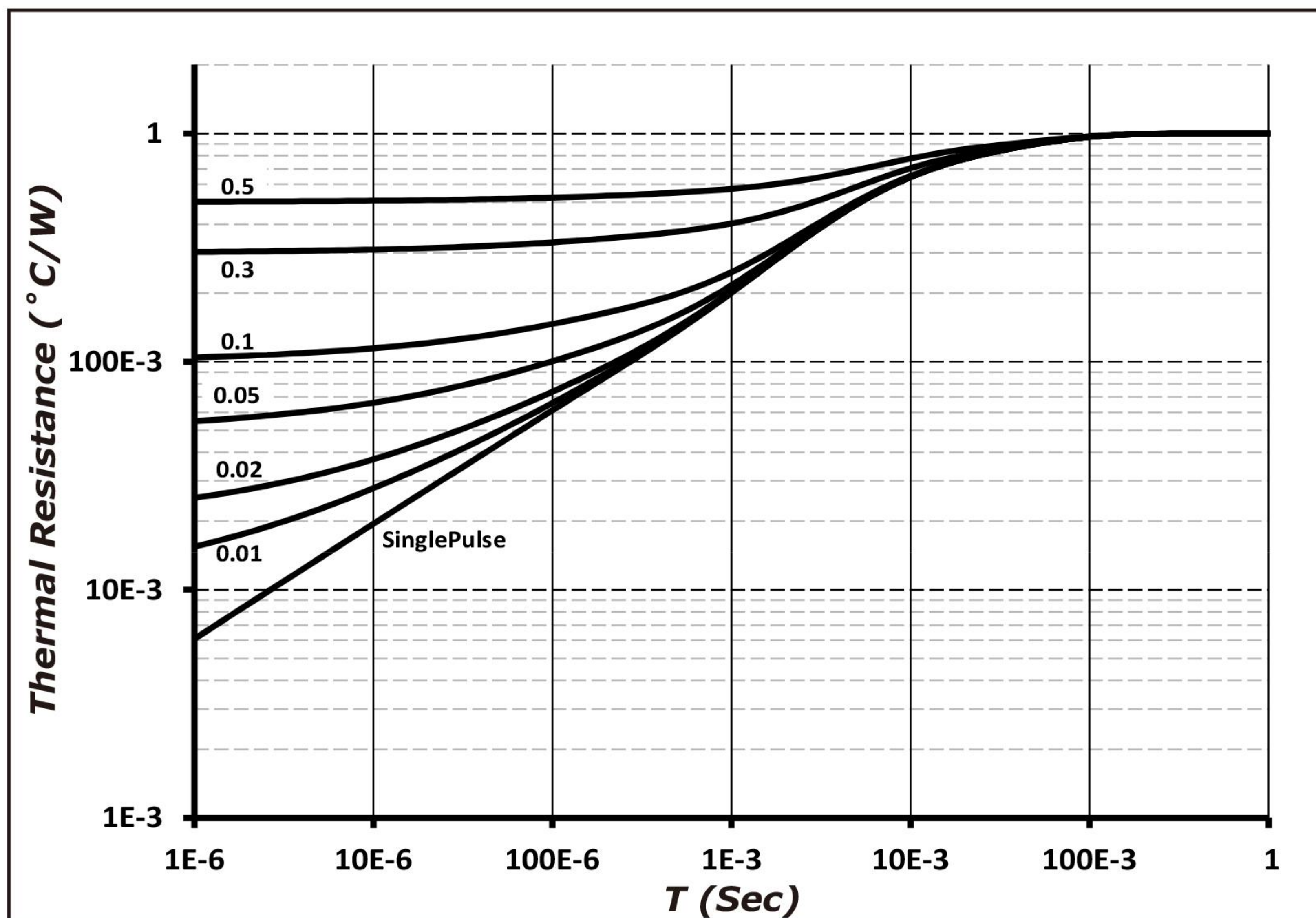
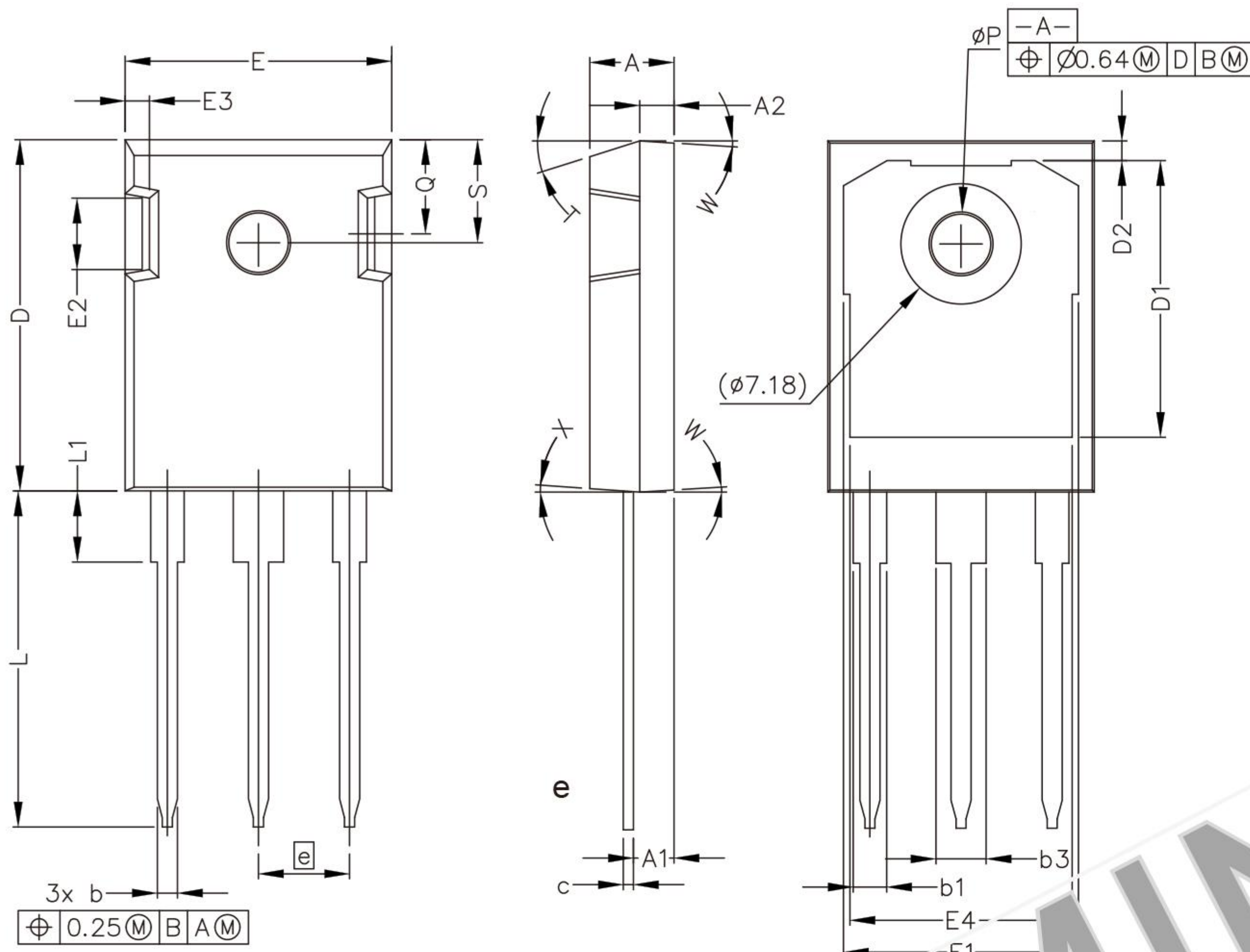


Figure 9. Transient Thermal Impedance

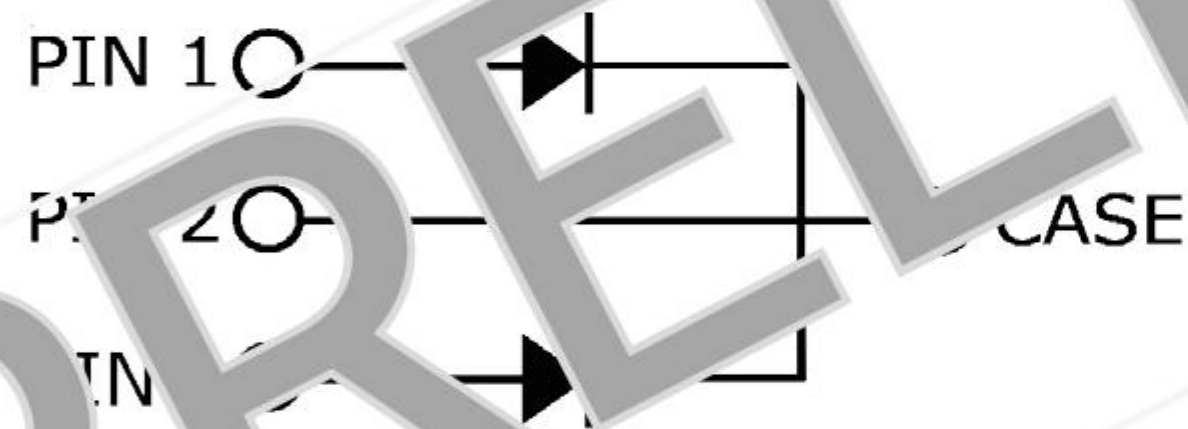
Package Dimensions

Package TO-247-3

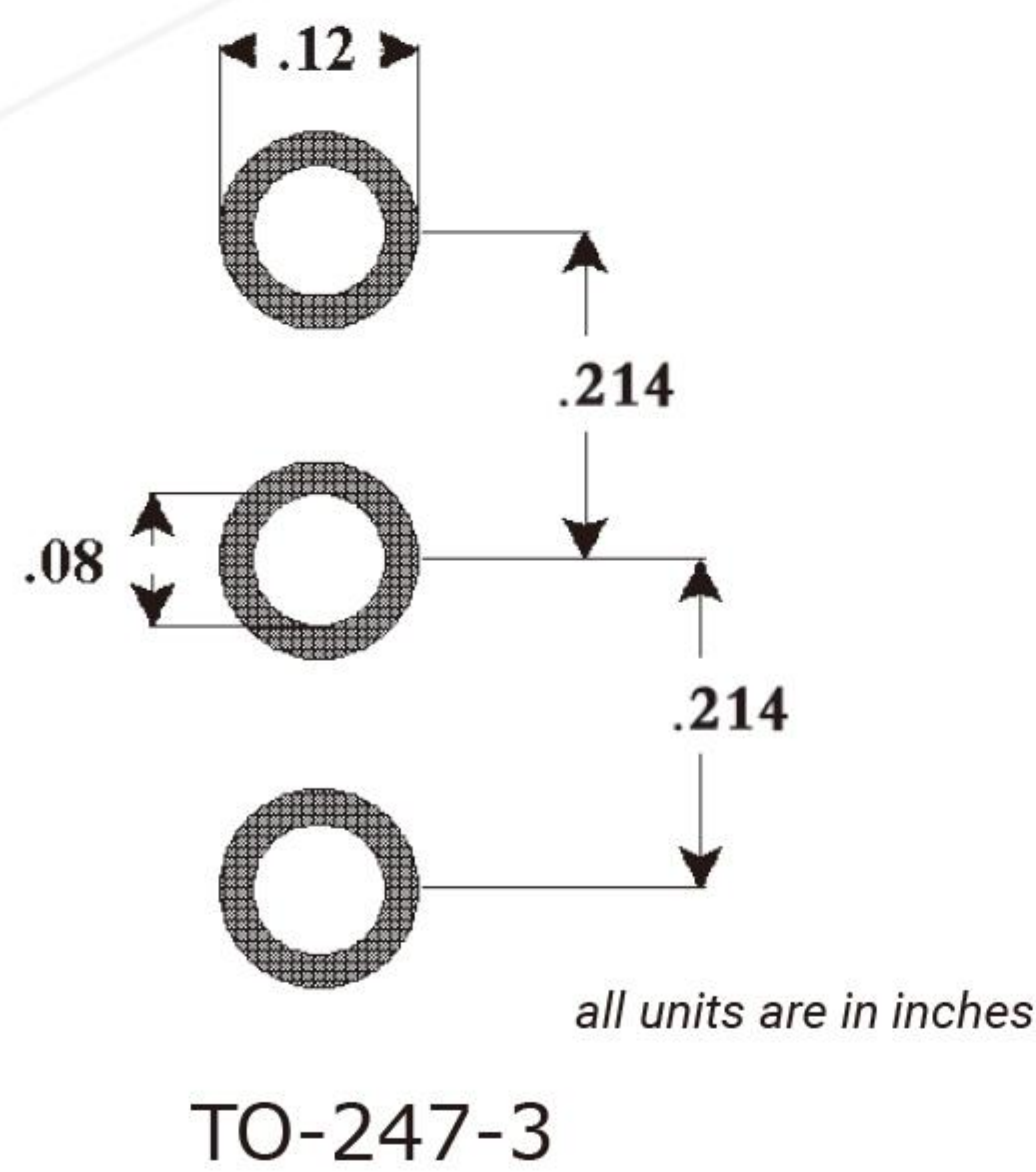


| POS | Inches | | Millimeters | |
|-----|-----------|------|-------------|-------|
| | Min | Max | Min | Max |
| A | .190 | .205 | 4.83 | 5.21 |
| A1 | .090 | .100 | 2.29 | 2.54 |
| A2 | .075 | .085 | 1.91 | 2.16 |
| b | .042 | .052 | 1.07 | 1.33 |
| b1 | .075 | .095 | 1.91 | 2.41 |
| b3 | .113 | .133 | 2.87 | 3.38 |
| c | .022 | .027 | 0.55 | 0.68 |
| D | .819 | .831 | 20.80 | 21.10 |
| D1 | .640 | .695 | 16.25 | 17.65 |
| D2 | .037 | .049 | 0.95 | 1.25 |
| E | .620 | .635 | 15.75 | 16.13 |
| E1 | .516 | .557 | 13.10 | 14.15 |
| E2 | .145 | .200 | 3.68 | 5.10 |
| E3 | .075 | .075 | 1.00 | 1.90 |
| E4 | .487 | .529 | 12.38 | 13.43 |
| e | .25 BSC | | 5.44 BSC | |
| L | .78 | .800 | 19.81 | 20.32 |
| L1 | .161 | .173 | 4.10 | 4.40 |
| N | 3 | | | |
| ØP | .133 | .144 | 3.51 | 3.65 |
| Q | .216 | .236 | 5.49 | 6.00 |
| S | .238 | .248 | 6.04 | 6.30 |
| T | 17.5° REF | | | |
| W | 3.5° REF | | | |
| X | 4° REF | | | |

PRELIMINARY

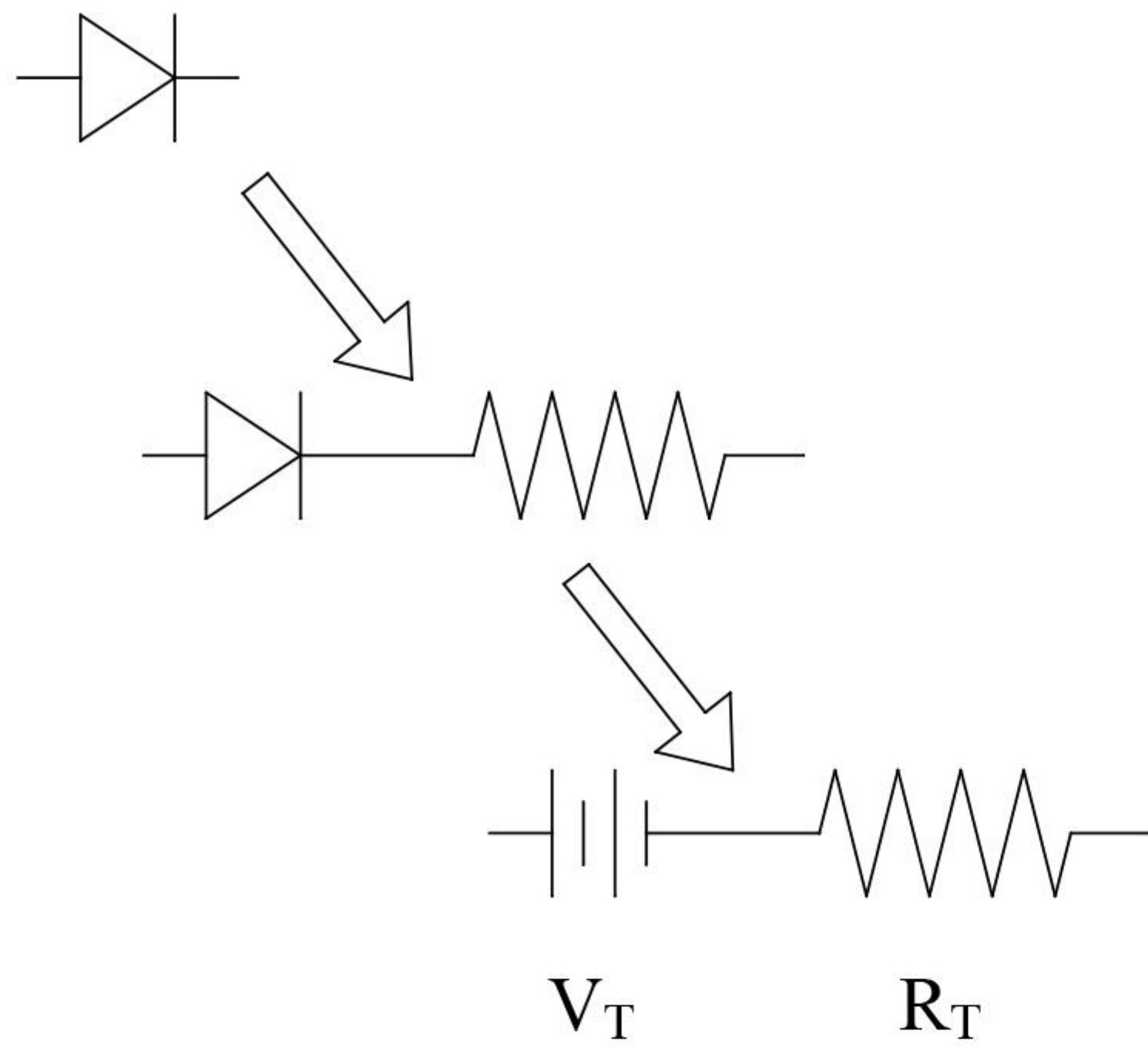


Recommended Solder Pad Layout



| Part Number | Package | Marking |
|-------------|----------|----------|
| C3D30065D | TO-247-3 | C3D30065 |

Diode Model (Per Leg)



$$V_{f_T} = V_T + I_f * R_T$$

$$V_T = 0.94 + (T_J * -1.0 * 10^{-3})$$

$$R_T = 0.027 + (T_J * 2.8 * 10^{-4})$$

Note: T_J = Diode Junction Temperature In Degrees Celsius,
valid from 25°C to 175°C